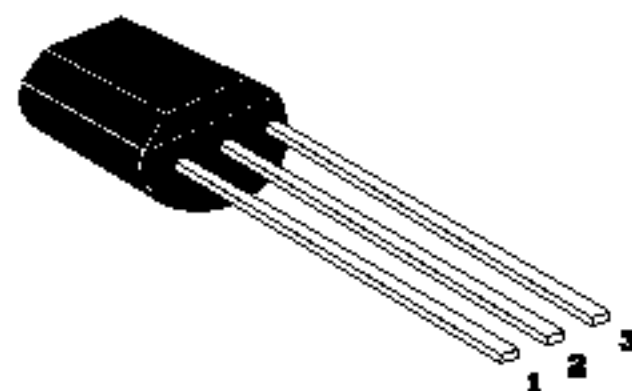




AMPLIFIER TRANSISTOR

- * Collector-Emitter Voltage $V_{CEO} = -150V$
- * Collector Dissipation $P_c(MAX) = 625 mW$

Package: TO-92



2

ABSOLUTE MAXIMUM RATINGS at $T_{amb} = 25^{\circ}C$

Characteristic	Symbol	Rating	Unit
Collector-Base Voltage	V_{cbo}	-160	V
Collector-Emitter Voltage	V_{ceo}	-150	V
Emitter-Base Voltage	V_{ebo}	-5	V
Collector Current	I_c	-600	mA
Collector Dissipation	P_c	625	mW
Junction Temperature	T_j	150	$^{\circ}C$
Storage Temperature	T_{stg}	-55~150	$^{\circ}C$

PIN:	1	2	3
STYLE			
NO.1	E	B	C

ELECTRICAL CHARACTERISTICS at $T_{amb} = 25^{\circ}C$

Characteristic	Symbol	Min	Typ	Max	Unit	Test Conditions
Collector-Base Breakdown Voltage	BV_{cbo}	-160			V	$I_c = 100\mu A, I_e = 0$
Collector-Emitter Breakdown Voltage	BV_{ceo}	-150			V	$I_c = 1mA, I_b = 0$
Emitter-Base Breakdown Voltage	BV_{ebo}	-5			V	$I_e = 10\mu A, I_c = 0$
Collector Cutoff Current	I_{cbo}			-50	nA	$V_{cb} = -120V, I_e = 0$
Emitter Cutoff Current	I_{ebo}			-50	nA	$V_{eb} = -3V, I_c = 0$
DC Current Gain	H_{fe1}	30				$V_{ce} = -5V, I_c = -1mA$
DC Current Gain	H_{fe2}	80		250		$V_{ce} = -5V, I_c = -10mA$
DC Current Gain	H_{fe3}	50				$V_{ce} = -5V, I_c = -50mA$
Collector-Emitter Saturation Voltage	$V_{ce(sat)}$			-0.20	V	$I_c = 10mA, I_b = 1mA$
Collector-Emitter Saturation Voltage	$V_{ce(sat)}$			-0.50	V	$I_c = 50mA, I_b = 5mA$
Base-Emitter Saturation Voltage	$V_{be(sat)}$			-1.00	V	$I_c = 10mA, I_b = 1mA$
Base-Emitter Saturation Voltage	$V_{be(sat)}$			-1.00	V	$I_c = 50mA, I_b = 5mA$
Output Capacitance	C_{ob}			6.00	pF	$V_{cb} = -10V, I_e = 0, f = 1MHz$
Current Gain-Bandwidth Product	fT	100		400	MHz	$V_{ce} = -10V, I_c = -10mA, f = 100MHz$
Noise Figure	NF			8	dB	$I_c = 250\mu A, V_{ce} = -5V, f = 10Hz \text{ to } 15.7kHz, R_s = 1K\Omega$